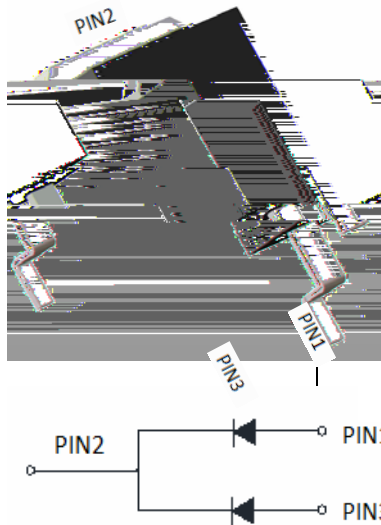


Schottky Diodes

Features

- | | |
|--|--|
| <ul style="list-style-type: none"> • High frequency operation • Low forward voltage drop • High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance • Guaranteed performance and JESD22-B102 | |
|--|--|



- **Polarity:** As marked

■ **Maximum Ratings** (T_a=25 °C) Unless otherwise specified

PARAMETER				SYMBOL	UNIT	MBRB1020CT	MBRB1035CT	MBRB1045CT	MBRB1050CT	MBRB1060CT
Device marking code						MBRB1020CT	MBRB1035CT	MBRB1045CT	MBRB1050CT	MBRB1060CT
Repetitive Peak Reverse Voltage				VRRM	V	20	10	10		
Current Squared Time @1ms≤t<8.3ms Tj=25				I²t	A²s			41		
Storage Temperature				Tstg				-55 ~ +150		
Junction Temperature				Tj			-55 ~ +125		-55 ~ +150	
Maximum instantaneous forward voltage drop per diode				VFM	V	IFM=5.0A	0.55		0.75	
Maximum DC reverse current at rated DC blocking voltage per diode				I _{RRM1}	mA	V _{RM} =V _{RRM} T _a =25		0.2		
				I _{RRM2}		V _{RM} =V _{RRM} T _a =100		20		
Note1:Pulse test:300uS pulse width,1% duty cycle Note2:Pulse test:pulse width 40mS										
						1 / 4				
S-B684 Rev.1.1,02-Aug-23				Yangzhou Yangjie Electronic Technology Co., Ltd.				www.21yangjie.com		



MBRB1020CT THRU MBRB1060CT

■Thermal Characteristics $T_a=25$ Unless otherwise specified

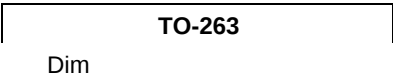
PARAMETER		SYMBOL	UNIT	MBRB1020CT	MBRB1035CT	MBRB1040CT	MBRB1050CT	MBRB1060CT
Thermal Resistance	Between junction and case	$R_{\theta J-C}$	$^{\circ}W$					
				2.0				

■P

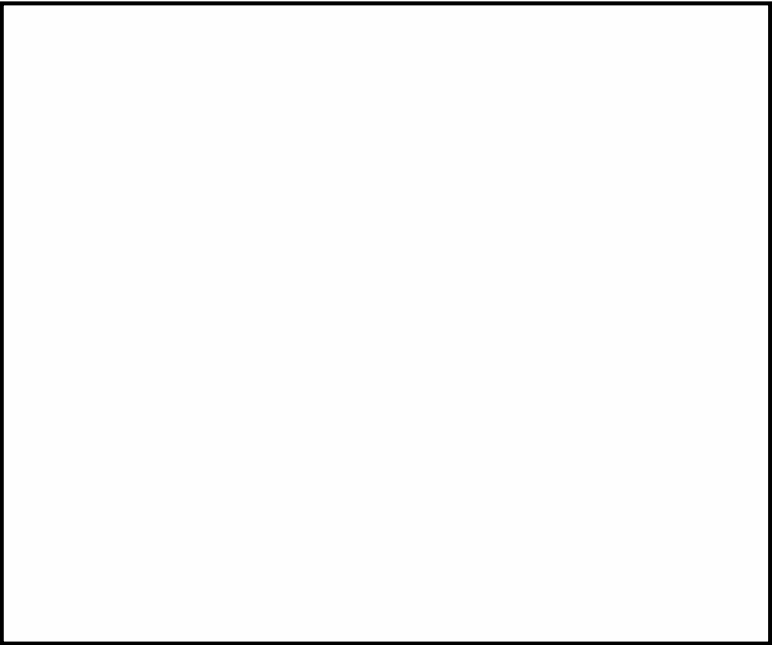


MBRB1020CT THRU MBRB1060CT

■Outline Dimensions



■Suggested Pad Layout



MBRB1020CT THRU MBRB1060CT